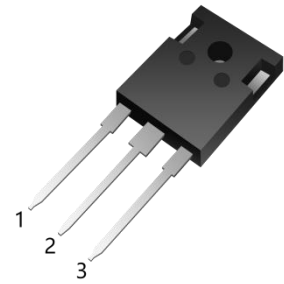
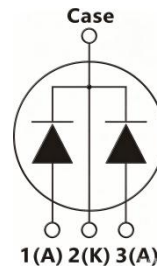


Silicon Carbide Schottky Diode

Parameter	Value	Unit
V_{RRM}	1200	V
I_F	60*	A
Q_C	306*	nC



TO-247-3L

Features

- Zero reverse recovery current
- Zero forward recovery voltage
- Temperature independent switching behavior
- High temperature operation
- High frequency operation

Applications

- Switched-Mode Power Supply
- Power Factor Correction
- Uninterruptible Power Supply
- Motor drives
- Photovoltaic inverters
- High-power adapters

Maximum Ratings (at $T_J=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V
Surge Peak Reverse Voltage	V_{RSM}	1200	V
Continuous Forward Current $T_C=25^\circ\text{C}$ $T_C=145^\circ\text{C}$	I_F	155* 60*	A
Non-Repetitive Forward Surge Current $T_C = 25^\circ\text{C}, t_p=10\text{ms}, \text{Half Sine Pulse}$	I_{FSM}	450*	A
Power dissipation $T_C = 25^\circ\text{C}, T_J = 175^\circ\text{C}$	P_{tot}	535*	W
Operating junction Range	T_j	-55 to +175	$^\circ\text{C}$
Storage temperature Range	T_{stg}	-55 to +175	$^\circ\text{C}$

* Per leg; **Per device

Thermal Characteristics

Parameter	Symbol	Typ.	Unit
Thermal resistance, junction – case.	R_{thJC}	0.28* 0.14**	°C/W

Electrical Characteristics(at $T_j=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Value			Unit
			Min.	Typ.	Max.	
DC blocking voltage	V_{DC}		1200			V
Diode forward voltage	V_F	$I_F=60\text{A}, T_j=25^\circ\text{C}$ $I_F=60\text{A}, T_j=175^\circ\text{C}$		1.45 1.88	1.61	V
Reverse current	I_R	$V_R=1200\text{V}, T_j=25^\circ\text{C}$ $V_R=1200\text{V}, T_j=175^\circ\text{C}$			150 400	μA
Total capacitive charge	Q_C	$V_R=1000\text{V}, T_j=25^\circ\text{C}$		306		nC
Total capacitance	C	$T_j=25^\circ\text{C}$ $V_R=1\text{V}, f=1\text{MHz}$ $V_R=400\text{V}, f=1\text{MHz}$ $V_R=800\text{V}, f=1\text{MHz}$		4960 240 174		pF

* Per leg **Per device

Typical Characteristics

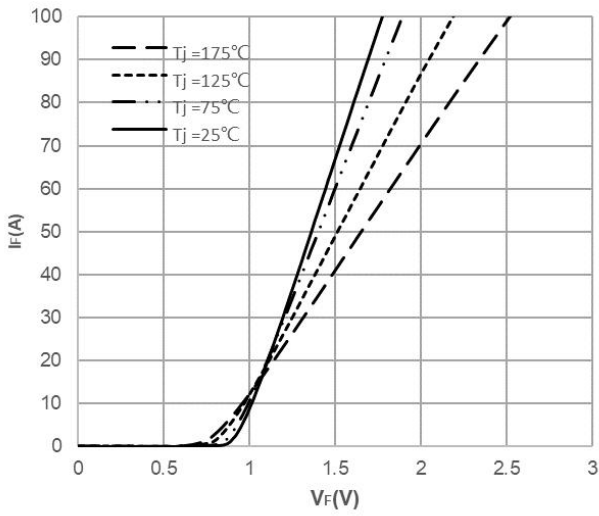


Fig1. Forward Characteristics

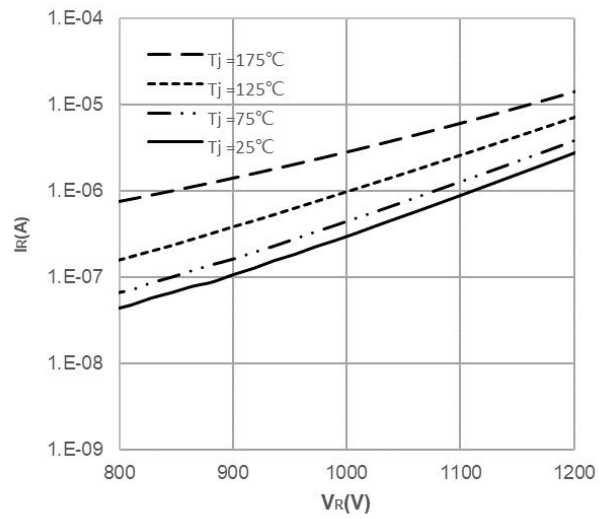


Fig2. Reverse Characteristics

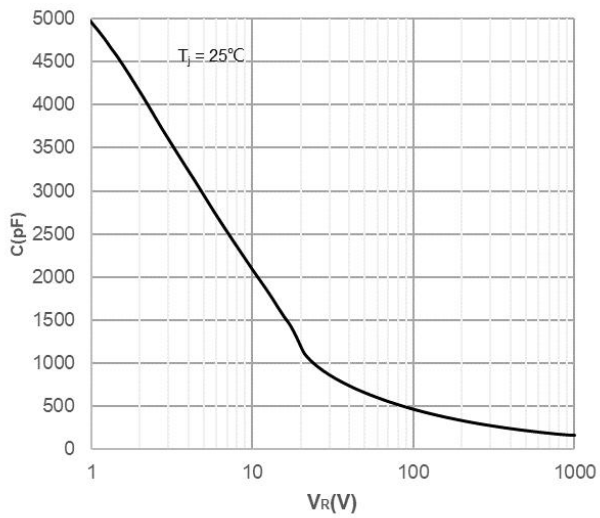


Fig3. Capacitance vs. Reverse Voltage

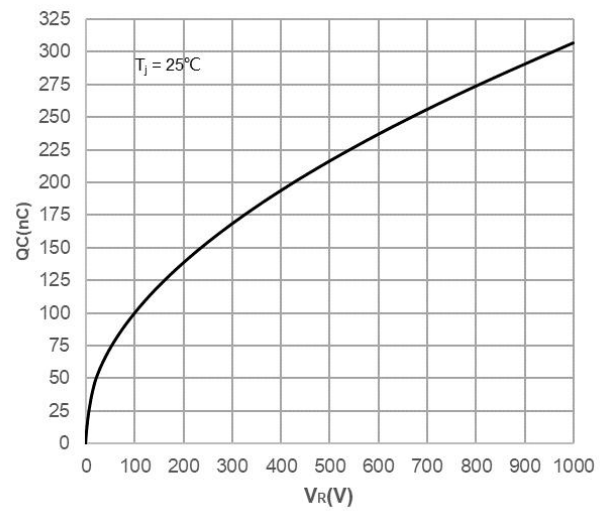
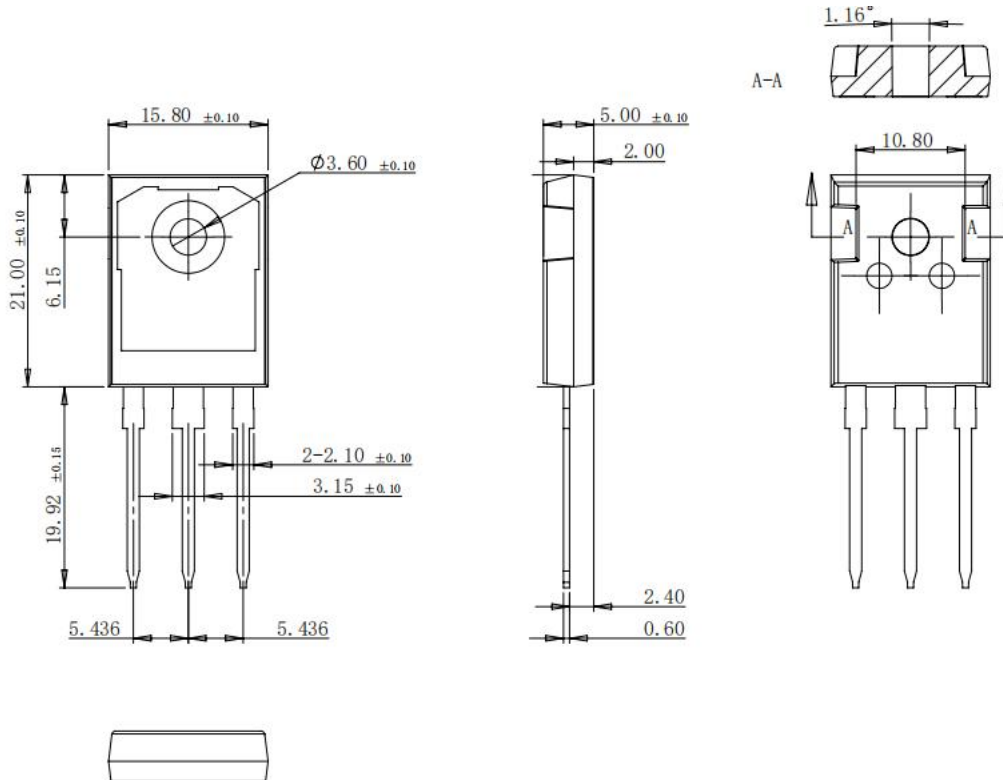


Fig4. Recovery Charge vs. Reverse Voltage

Package Outlines(Unit:mm)

TO-247-3L



*Important Usage Information and Disclaimer

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